

Type Designator: 2SB365

Material of Transistor: Ge

Polarity: PNP

Maximum Collector Power Dissipation (P_c): 0.15 W

Maximum Collector-Base Voltage $|V_{cb}|$: 20 V

Maximum Emitter-Base Voltage $|V_{eb}|$: 12 V

Maximum Collector Current $|I_c \text{ max}|$: 0.4 A

Max. Operating Junction Temperature (T_j): 75 °C

Forward Current Transfer Ratio (h_{FE}), MIN: 30

Noise Figure, dB: -

Package: TO1